# **825 Positive Photoresist**

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Positive Working Photoresist Systems for the Semiconductor Industry

# **DESCRIPTION**

Arch Chemicals 825 is a positive photoresist which offers excellent processing latitude and high thermal stability. Arch Chemicals 825 is a single-solvent resist which contains ethyl 3-ethoxypropionate as the solvent.

Catalog No	898470
Solids Content	31.03 - 3.0%
Viscosity	33.5 - 36.5 cSt
Water Content	
Nominal Film Thickness	1.25µm
Total Metal Content	500 ppb total

# **FEATURES**

Arch Chemicals 825 is a production viable system for broadband, g-line, and i-line exposure tools. It exhibits excellent photospeed when used with either TMAH or Na<sup>+</sup> based developers. The thermal stability of Arch Chemicals 825 equals or exceeds products currently available for production use. Arch Chemicals 825 displays process latitude capable of sustaining 0.8 production processes (g-line).

Ethyl 3-ethoxypropionate, the single solvent in Arch 825 is a "safer solvent." Arch 825 contains no cellosolve acetate. Arch 825 is an excellent replacement for Arch 820 and other EGMEA containing resists.

# **BENEFITS**

- Excellent photospeed allows greater production throughout on all types of exposure equipment.
- Thermal stability characteristics (>130°C) provide superior plasma etch resistance in harsh environments, even without DUV stabilization.
- Solvent formulation permits a safer workplace environment.
- Excellent process latitude without the necessity of a post-exposure bake.
- Single-solvent system allows for outstanding coating uniformity, resulting in improved CD control.
- Low trace metal levels help maintain high yields.

# **PROCESSING**

### Substrate Preparation:

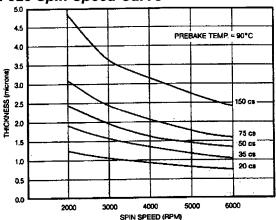
For optimal process consistency and adhesion, substrates should be appropriately treated. Dehydration baking and use of HMDS vapor prime methods will ensure a repeatable, optimized process.

### **RESIST COATING**

Arch 825 can be coated using typical methods. For maximum uniformity, the following coat process is recommended:

- 1. Dynamic Dispense @ 700 1000 rpm
- Spread for 1- 2 seconds at same time as step 1
- 3. Ramp at 10 krpm/sec to final spin speed of 3- 6K rpm
- 4. Spin for 25 35 seconds

# Arch 825 Spin Speed Curve



# **PREBAKE**

Processing recommendations for convection oven and hotplate prebake are listed below:

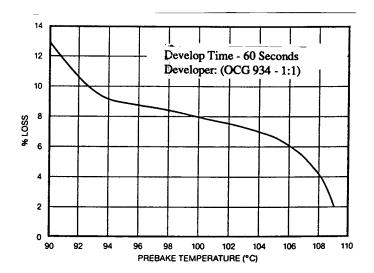
# Convection Oven with Forced Air

100-110°C for 15 - 30 minutes

## Hotplate

105-115°C for 45 - 60 seconds

# Film Thickness Loss vs Prebake Temperature



# **Exposure**

OCG 825 is compatible with exposure tools which utilize radiation in the range of 320-436 nanometers. Exposure energies are highly dependent on the processing parameters in use, and must be determined for each individual process. However, some typical exposure conditions for various tools are shown below:

SVG Micralign 340 HT Projection Mask Aligner

Resist Thickness	1.2 µm (on SiO <sub>2</sub> )
Scan Speed	500 - 600
Aperture	1
Slit Width	

SVG Micralign 660 Projection Mask Aligner

Resist Thickness	1.2 μm (on SiO₂)
Energy	40 - 60 mJ/cm2 (UV-4)

-Ultratech 1000 1:1 Stepper (g-line)

Resist Thickness	1.2 μm (on SiO <sub>2</sub> )
Exposure	250 - 270 msecs

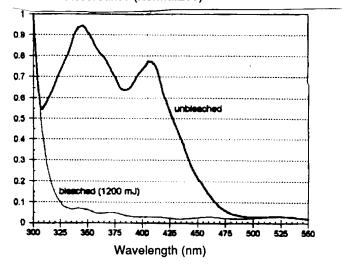
GCA 6300 5:1 Stepper (g-line)

Resist Thickness	1.2 μm (on SiO <sub>2</sub> )
Exposure	230 - 290 msecs

Canon 0.43, 5x
Resist Thickness......1.2 μm (on SiO<sub>2</sub>)
Exposure.....120 mJ/cm<sup>2</sup>

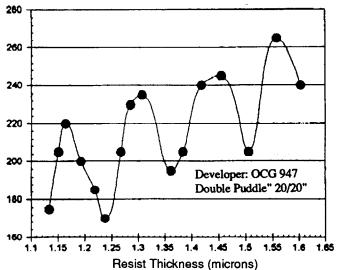
# **Absorbance Characteristics**

Absorbance (Normalized)



# Exposure (E°) vs. Film Thickness (g-line)

E-zero (milliseconds)



Typical g-line stepper images

Substrate: Silicon

Film: 1.2µm resist thickness

Prebake: 85°C, 60 seconds, hotplate Exposure: Canon, 0.43 NA, 5x, 120 mJ/cm2

PEB: 95°C, 60 seconds, hotplate

Develop: HPRD 428 (60:40), 80 second immersion







0.8µm l/s pairs

0.9µm l/s pairs

1.0µm l/s pairs

# Typical SVG Micralign 600 images

Substrate:

Polysilicon

Film:

1.2µm resist thickness

Prebake:

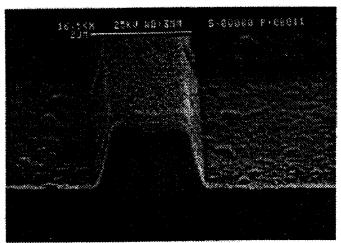
110°C, 45 seconds, hotplate

Exposure:

SVG 600 HT, aperture 2, 70 mJ/cm2

Develop:

Na+ based developer, 45 second immersion



2.0µm isolated line

# Typical Ultratech stepper images

Substrate:

Polysilicon

Film:

1.2µm resist thickness

Prebake:

85°C, 60 seconds, hotplate

Exposure:

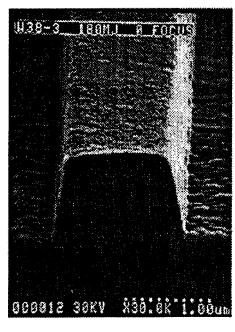
Ultratech 1100, 1x, 0.34 NA, 180 mJ/cm<sup>2</sup>

PEB:

95°C, 60 seconds, hotplate

Develop:

OCG 934 (3:2), 30/30 sec. double puddle



1.6µm isolated line

### DEVELOPMENT

To develop Arch 825 after exposure via any of the above methods, process according to the following guidelines:

### Spray Puddle Process:

(Use OCG 934 (3:2) developer at  $21 \pm 1^{\circ}$ C)

- 1. Spray 4 seconds while spinning at 200 rpm
- 2. Puddle static time: 20 25 seconds
- 3. Replenish spray 3 seconds at 200 rpm
- 4. Overlay 2 3 seconds (developer/DI water)
- 5. Rinse 15 20 seconds with DI water
- 6. Spin dry

### **Immersion Process:**

(Use OCG 934 (3:2) developer at  $21 \pm 1^{\circ}$ C)

- 1. Immerse for 60 seconds with continuous agitation
- 2. Rinse with DI water
- 3. Dry

Use of a nitrogen blanket is recommended to prolong bath life of the developer and maintain consistent activity.

Other developer dilutions may be used. At higher developer concentrations, changes in the prebake time or temperature may be necessary to minimize the unexposed resist loss during development. For higher contrast, more dilute developers may require longer develop times or increased exposure doses. Arch 825 is also compatible with other development processes.

# **POSTBAKE & ETCH PERFORMANCE**

Recommended postbake processes for convection oven and hotplate are shown below:

# Convection oven with forced air:

130° - 140°C for 30 minutes

# Hotplate Oven:

140° - 150°C for 60 seconds

Postbaking will generally remove remaining solvents and increase resistance to plasma and wet etching without causing perceptible image changes. At temperatures above 150°C, critical dimensions may not be affected, but other image structure changes, such as top rounding may result. These changes are most noticeable in thicker coatings and at the edges of larger resist fields. Post treatment using DUV flood exposure of similar processes will further enhance high temperature stability.

### Thermal stability of Arch 825

Coat:

1.2µm resist film

Softbake:

110°C, 45 seconds, hotplate

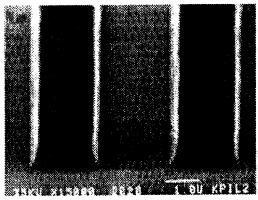
Expose:

Micralign 240

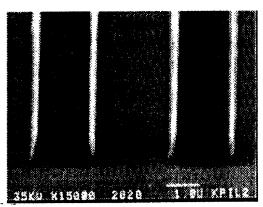
Develop:

Na+ based developer, immersion,

60 seconds at 20°C



No Postbake



Convection Bake (130°C, 30 minutes)

# **STRIPPING**

Arch 825 can be removed with all standard wet or dry tech-Due to its high thermal stability, it is effectively stripped even from wafers that have been subjected to harsh dry etch and ion implant processes.

### Material Properties:

Water Content (by weight).... < 0.5%

Refractive Index......1.64 (dry film, 450nm) Solvent..... ethyl 3-ethoxypropionate

(EEP)

Filtration......0.2 µm

STORAGE: Store only in original container in a dry area at 10 - 21°C (50 - 70°F). Do not store in direct sunlight. For maximum shelf life, store at 10°C (50°F).

HANDLE WITH CARE: Photochemically reactive. Consult the appropriate material Safety Data Sheet for current specific handling and safety information.

**CAUTION:** Combustible. Keep away from heat and flame. Contents may develop pressure on prolonged exposure to heat. Store in cool place. Keep containers closed.

### PRODUCT STEWARDSHIP:

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32-3-252-46-31

Please refer to the Material Safety Data Sheet (MSDS) for complete information on Storage and Handling, Toxicological Properties, Personal Protection, First Aid, Spill and Leak Procedures, and Waste Disposal. To order an MSDS, call your nearest Arch Chemicals sales office or the MSDS Control Group at (800) 511-MSDS (6737). Before using or handling this product, the MSDS should be thoroughly reviewed.

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